

Schottky Barrier Diodes

(Pb) Lead(Pb)-Free

Features:

- * High Reliability
- * Low Reverse Current and Low Forward Voltage

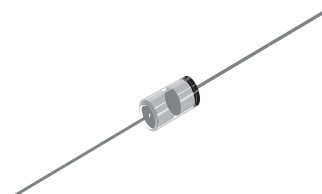
Applications:

- * Low Current Rectification and High Speed Switching

Mechanical Data:

- *Case : DO-35 Glass Case
- *Weight : Approx 0.13 gram

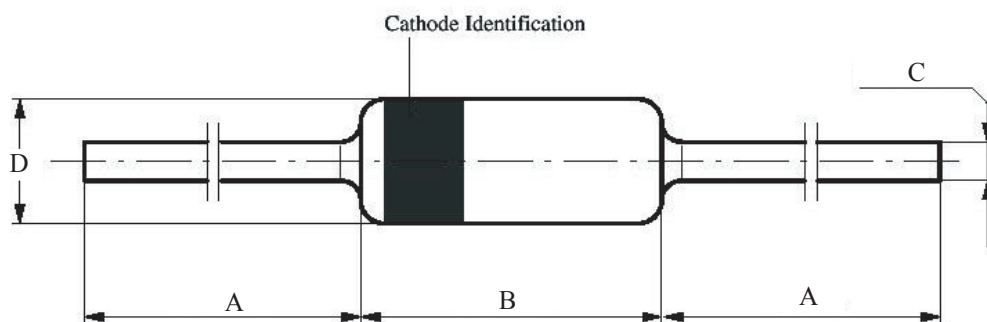
**SMALL SIGNAL
SCHOTTKY DIODES
30m/50m AMPERES
40/45VOLTS**



DO-35

DO-35 Outline Dimensions

Unit:mm



	A		B		C		D	
DIM	Min	Max	Min	Max	Min	Max	Min	Max
DO-35	26.0	-	-	4.20	-	0.55	-	2.0

Maximum Ratings ($T_A=25^{\circ}\text{C}$ Unless otherwise noted)

Characteristic	Symbol	1N60	1N60P	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	40	45	V
Forward Continuous Current	I_F	30	50	mA
Peak Forward Surge Current ($t_p \leq 1\text{s}$)	I_{FSM}	150	500	mA
Thermal Resistance Junction to Ambient ⁽¹⁾	$R_{\theta JA}$	250		K/W
Operating Temperature Range	T_J	125		$^{\circ}\text{C}$
Storage Temperature Range	T_{STG}	-65 to +125		$^{\circ}\text{C}$

1. On PC board 50mm x 50mm x 1.6mm

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ Unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Forward Voltage $I_F=1\text{mA}$ 1N60 1N60P $I_F=30\text{mA}$ 1N60 $I_F=200\text{mA}$ 1N60P	V_F	-	0.32 0.24 0.65 0.65	0.5 0.5 1.0 1.0	V
Reverse Current $V_R=15\text{V}$ 1N60 1N60P	I_R	-	0.1 0.5	0.5 1.0	μA
Junction Capacitance $V_R=1\text{V}$, $f=1\text{MHz}$ 1N60 $V_R=10\text{V}$, $f=1\text{MHz}$ 1N60P	C_J	-	2.0 6.0	-	pF
Reverse Recovery Time $I_F=I_R=1\text{mA}$, $I_{rr}=1\text{mA}$, $R_C=100\Omega$	T_{rr}	-	-	1.0	nS